

12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN# 20140709001 Elimination of Tungsten at Metal One on select devices in the CS80 process Change Notification / Sample Request

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

We request you acknowledge receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If you require samples or additional data to support your evaluation, please request within 30 days.

The changes discussed within this PCN will not take effect any earlier than **90** days from the date of this notification, unless customer agreement has been reached on an earlier implementation of the change. This notification period is per TI's standard process.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice, contact your local Field Sales Representative or the PCN Manager (PCN www admin team@list.ti.com).

Sincerely,

PCN Team SC Business Services Phone: +1(214) 480-6037 Fax: +1(214) 480-6659

PCN# 20140709001 Attachment: 1

Products Affected:

According to our records, there are the affected device(s) that you have purchased within the past twenty-four (24) months. Technical details of this Product Change follow on the next page(s).

PCN Number:			20140709001							PCN Date: 7/17/2014			7/17/2014			
select device			ngsten at Metal One with standard aluminum metallization architecture on in the CS80 Fab process at Maine Fab													
Customer Contact:			PCN A	<u>lan</u>	age	Phon	e: +1()	21	4)480-603	7	D	ept:	Qua	ality Services		
*Proposed 1 st Ship Date			te:					timated Sample ailability:				Date Provided at Sample request				
Chan	ge Ty	/pe:														
	Assem	bly S	Site				Assembly	Process					Assem	Assembly Materials		
	Design				Electrical Spec									Mechanical Specification		
=	est Si				Packing/Shipping/Labeling				_		_		Test Process			
			p Site		Ļ		Wafer Bump Material				_			np Process		
W	Vafer	Fab	Site			4		Wafer Fab Materials					Wafer Fab Process			
							Part number change PCN Details									
	•		. 61				PCI	N Deta		<u>S</u>						
Desci	riptio	n ot	Change													
Curre Chip MAIN				rchite	chitecture on select devi			devices	ement of Tungsten at Metal one with standard ces in the CS80 Fab process at Maine Fab. er Metal One Composition TiW/W							
New																
	Site		Fab Pro					meter	•							
MAI	NEFA	B	CS80		200mm				TiN/AL							
Reas	on fo	r Ch	ange:													
Contir	nuity	of su	ipply.													
Antic	ipate	d in	npact on	Form	1, F	it,	Function	, Qualit	у	or Reliabil	ity	(p	ositiv	/e /	negative):	
None																
Chan	ges t	o pr	oduct ide	entifi	ca	tio	n resultin	g from	th	is PCN:						
None																
Produ	uct A	ffec	ted:													
DS36C200M/NOPB			LMS	33	460)MG	LM	IV3	42MMX/J700	0264	40	LMV	′602N	/AX/NOPB		
	DS36C200MX/NOPB			LMS	LMS33460MG/NOPB					42MMX/MES				LMV602MM/NOPB		
	DS90C031TM				LMV2011MA/NOPB				LMV342MMX/NOPB					LMV602MMX/NOPB		
DS90	DS90C031TM/NOPB			LMV	/20	111	4AX	LM	IV3	42MMX/S50	010	99	LMV	716	4M/NOPB	
DS90C031TMX/NOPB			LMV	LMV2011MAX/NOPB				LMV342MMX/S7002484				LMV	LMV716MMX/NOPB			
DS90C032TM			LMV2011MF				LM	LMV342MMX/S7002574				LMV	LMV7219M5			
DS90C032TM/NAK2			LMV	LMV2011MF/NOPB				LMV358M				LMV	LMV7219M5/NOPB			
DS90C032TM/NOPB			LMV	LMV2011MFX/NOPB				LMV358M/NOPB				LMV	LMV7219M5X			
DS90	DS90C032TMX			LMV	LMV331M5				LMV358MM				LMV	LMV7219M5X/NOPB		
DS90C032TMX/NOPB			LMV	LMV331M5/MESN				LMV358MM/DRSN					LMV7219M5X/S5000707			
DS90	DS90C401M			LMV	/33	1M!	5/NOPB	LM	V3	58MM/NOPE	3		LMV	7219	M5X/S7002242	
DS90C401M/NOPB			LMV	LMV331M5X				LMV358MMX/E7002183					LMV7219M7			
DS90	DS90C401MX			LMV	LMV331M5X/NOPB				LMV358MMX/NOPB					LMV7219M7/NOPB		
DS90C401MX/NOPB				LMV331M7				LMV358MMX/S7002186					LMV7219M7X			
	DS90C402M			LMV331M7/NOPB					LMV358MMX/SL110547					LMV7219M7X/NOPB		
DS90C402M/NOPB			LMV331M7X					LMV358MX					LMV7275MF			

DS90C402MX	LMV331M7X/NOPB	LMV358MX/DRSN	LMV7275MF/NOPB
DS90C402MX/NOPB	LMV339M	LMV358MX/E7002867	LMV7275MFX/NOPB
EMB1462MM/NOPB	LMV339M/NOPB	LMV358MX/MESN	LMV7275MGX/EMSN
EMB1462MME/NOPB	LMV339MT	LMV358MX/NOPB	LMV7291MG
EMB1462MMX/NOPB	LMV339MT/NOPB	LMV393M	LMV7291MG/67
LM8364BALMF20	LMV339MTX	LMV393M/NOPB	LMV7291MG/NOPB
LM8364BALMF20/NOPB	LMV339MTX/NOPB	LMV393MM	LMV7291MGX/NOPB
LM8364BALMFX20/NOPB	LMV339MX/NOPB	LMV393MM/NOPB	LMV762MA
LM8365BALMF27	LMV341MG/NOPB	LMV393MMX	LMV762MA/NOPB
LM8365BALMF27/NOPB	LMV341MGX/NOPB	LMV393MMX/E7001611	LMV762MAX
LM8365BALMFX27/NOPB	LMV342MA/NOPB	LMV393MMX/ELLI971	LMV762MAX/NOPB
LM8365BALMFX45/NOPB	LMV342MAX	LMV393MMX/NOPB	LMV762MM
LMP2011MA/NOPB	LMV342MAX/E7001823	LMV393MX	LMV762MM/NOPB
LMP2011MAX/NOPB	LMV342MAX/E7002870	LMV393MX/NOPB	LMV762MMX
LMP2011MF	LMV342MAX/J7002023	LMV393MX/S5000873	LMV762MMX/NOPB
LMP2011MF/NOPB	LMV342MAX/NOPB	LMV601MG/NOPB	SM73303MM/NOPB
LMP2011MFX/NOPB	LMV342MAX/S7002483	LMV601MGX/NOPB	SM73303MME/NOPB
LMP2014MT/NOPB	LMV342MM/NOPB	LMV602MA/NOPB	SM73303MMX/NOPB
LMP2014MTX/NOPB			

Qualification Data: (Approved: 5/21/2014)									
This qualification has been developed for the validation of this change. The qualification data will									
validate that the proposed change meets the applicable released technical specifications.									
Qualification Device 1: DS90C401M (MSL LEVEL1-260C)									
Wafer Fab Site:	MAIN	FAB Wafer Fab Process: CS80							
Wafer Diameter:	200n	m							
Qualification: Plan	⊠ Te:	st Results							
Reliability Test		Conditions	Sample Size / Fail						
·				Lot#1	Lot#2	Lot#3			
Electrical Characterization		Per Datash	Pass	-	-				
ESD HBM		1000V	3/0	3/0	3/0				
ESD CDM		250V	3/0	3/0	3/0				
Latchup		(per JESD7	6/0	6/0	-				
**Preconditioning: MSL1@260C									
Qualification Device 2: LMV772QMM (MSL LEVEL1-260C)									
Wafer Fab Site:	MAIN	IE FAB	E FAB Wafer Fab Process: CS80						
Wafer Diameter:	200n	ım							
Qualification: Plan Test Results									
Reliability Test		Conditions		Sample Size / Fail					
Reliability Test				Lot#1	Lot#2	Lot#3			
Electrical Characterization		Per Datasheet spec		Pass	-	-			
ESD HBM		1000V	3/0	3/0	3/0				
ESD CDM		250V	3/0	3/0	3/0				
Latchup		(per JESD7	6/0	6/0	-				
**Preconditioning: MSL1@260C									

Qualification Device 3: LMV932M (MSL LEVEL1-260C)							
Wafer Fab Site:	MAINE FAB	Wafer Fab Process:	CS80				
Wafer Diameter:	200mm						
Qualification: Plan Test Results							
Reliability Test	Conditions		Sam	Sample Size / Fail			
Reliability Test	Conditions		Lot#1	Lot#2	Lot#3		
Electrical Characterization	Per Datash	Per Datasheet spec			-		
ESD HBM	1000V	1000V			3/0		
ESD CDM	250V	250V			3/0		
Latchup	(per JESD	78)	6/0	6/0	-		
**Life Test	150C (500	Hrs)	80/0	80/0	-		
**Preconditioning: MSL1@260C							

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com